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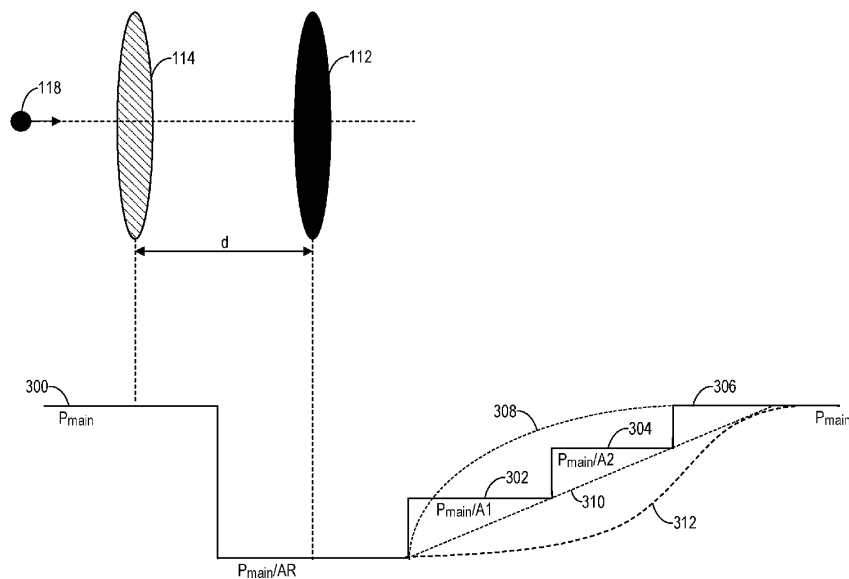


Figure 3

(57) Abstract: A semiconductor wafer is inspected using a main laser beam and a secondary laser beam. The secondary laser beam leads the main laser beam and has lower power than the main laser beam. Using the secondary laser beam, a particle is detected on the semiconductor wafer having a size that satisfies a threshold. In response to detecting the particle, the power of the main laser beam and the power of the secondary laser beam are reduced. The particle passes through the main laser beam with the main laser beam at reduced power. After the particle has passed through the main laser beam with the main laser beam at the reduced power, the power of the main laser beam and the power of the secondary laser beam are restored in a controlled manner that is slower than a single step.

[Continued on next page]

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